

제22회 한국반도체학술대회

2015년 2월 10일(화) - 12일(목), 인천 송도컨벤시아

K. Memory (Design & Process Technology) 분과

Room E
1F / 108호

2015년 2월 12일(목) 13:10-14:40

[TE2-K] PCRAMs, SRAMs, TFET and NEM Memories

좌장: 이재규 (삼성전자), 백승재 (한경대학교)

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| TE2-K-1 | 13:10-13:25 | Nonvolatile Memory Application of Tunneling Field-Effect Transistors
Woo Young Cheon and Woo Young Choi
Department of Electronic Eng., Sogang Univ. |
| TE2-K-2 | 16:05-16:20 | New Efficient Error Control Technique for 3D-Integrated SRAM
Heung Sun Yoon, Jong Kang Park, and Jong Tae Kim
School of Electronic and Electrical Eng., Sungkyunkwan University |
| TE2-K-3 | 13:40-13:55 | Modeling Statistics of Data Retention in PC-RAM by Phase-Field Method
Yongwoo Kwon ¹ and Dae-Hwan Kang ²
¹ Department of Materials Science and Engineering, Hongik University,
² Semiconductor R&D Center, Samsung Electronics Co., Ltd., |
| TE2-K-4 | 13:55-14:10 | Phase Change Analysis of Ge₂Sb₂Te₅ Nanowires with Joule Heating WN Electrodes
Jun-Young Lee, Jeong-Hyeon Kim, Jae-Hyun Han, and Jong-Souk Yeo |
| TE2-K-5 | 14:10-14:25 | Bipolar Resistive Switching of Amorphous Ge₂Sb₂Te₅ Thin Film without Involving Phase Change
Sijung Yoo, Taeyong Eom, Taehong Gwon, and Cheol Seong Hwang
Department of Materials Science and Engineering and Inter-university
Semiconductor Research Center, Seoul National University |
| TE2-K-6 | 14:25-14:40 | Zigzag Multi-Bit Nano-Electromechanical Memory Cells
Jae Hwan Han, Yong Jun Kim, Tae Min Cha, and Woo Young Choi
Department of Electronic Eng., Sogang University |